









# **CEM3133**

## -30V Δ 14mΩ Δ -9.3A Δ Si MOSFET

SILICON Si MOSFET ▲ SMD type
P-channel enhancement mode
UL94V-0 rated flame retardant epoxy
SO8 package ▲ MSL 3

Super high dense cell density for extremely low R<sub>DS(ON)</sub> **High power and current handling capability** 

## **MAXIMUM RATINGS**

Parameter (T <sub>A</sub> = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	-30V
Gate-Source Voltage	V <sub>GS</sub>	±25V
Continuous Drain Current	I <sub>D</sub>	-9.3A
Pulsed Drain Current Note 1	I <sub>DM</sub>	-37.2A
Maximum Power Dissipation	P <sub>D</sub>	2.5W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

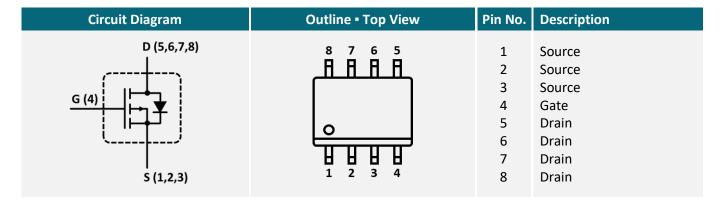
## THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>TH_JA</sub>	50°C/W

## **APPLICATIONS**

DC/DC	DC	Load	Power	USB	ì
Converter	Fan	Switches	Banks	Storage	1
			4	¥	

## **PIN DESCRIPTION**





## **ELECTRICAL CHARACTERISTICS** ▲ T<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = -250\mu A$	$BV_{DSS}$	-30			V
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I <sub>DSS</sub>			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V$ , $V_{DS} = 0V$	$I_{GSSF}$			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	$I_{GSSR}$			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	$V_{GS(th)}$	-0.8		-2	V
Static Drain-Source On-Resistance	$V_{GS} = -10V$ , $I_D = -4A$	R <sub>DS(ON)</sub>		14	18	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -4.5V$ , $I_D = -2A$	R <sub>DS(ON)</sub>		21	26	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = -15V$ , $V_{GS} = 0V$ , $f = 1MHz$	C <sub>ISS</sub>		1710		pF
Output Capacitance	$V_{DS} = -15V$ , $V_{GS} = 0V$ , $f = 1MHz$	Coss		260		pF
Reverse Transfer Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		185		pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{DD}$ = -24V, $V_{GS}$ = -10V, $I_D$ = -1A, $R_{G(ext)}$ = $6\Omega$	t <sub>D(ON)</sub>		16		ns
Turn-On Rise Time	$V_{DD}$ = -24V, $V_{GS}$ = -10V, $I_D$ = -1A, $R_{G(ext)}$ = $6\Omega$	t <sub>R</sub>		8		ns
Turn-Off Delay Time	$V_{DD}$ = -24V, $V_{GS}$ = -10V, $I_D$ = -1A, $R_{G(ext)}$ = $6\Omega$	t <sub>D(OFF)</sub>		75		ns
Turn-Off Fall Time	$V_{DD}$ = -24V, $V_{GS}$ = -10V, $I_D$ = -1A, $R_{G(ext)}$ = $6\Omega$	t <sub>F</sub>		36		ns
Total Gate Charge	$V_{DS} = -24V$ , $V_{GS} = -4.5V$ , $I_{D} = -1A$	$Q_{G}$		18		nC
Gate Source Charge	$V_{DS} = -24V$ , $V_{GS} = -4.5V$ , $I_{D} = -1A$	Q <sub>GS</sub>		3.4		nC
Gate Drain Charge	$V_{DS} = -24V$ , $V_{GS} = -4.5V$ , $I_{D} = -1A$	$Q_{GD}$		7.1		nC
<b>Drain-Source Diode Characteristics a</b>	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		I <sub>S</sub>			-2	Α
Drain-Source Diode Forward Voltage Note 3	$V_{GS} = 0V$ , $I_S = -2A$	$V_{SD}$			-1.2	V

#### Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, t ≤ 10 sec
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.



## REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

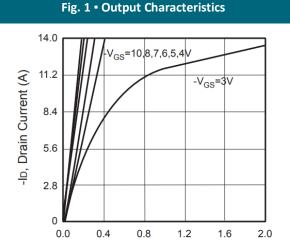


Fig. 2 • Transfer Characteristics

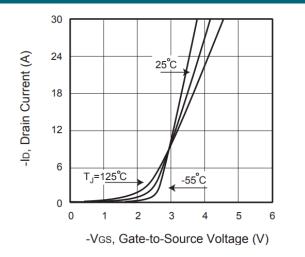


Fig. 3 • Capacitance

-VDS, Drain-to-Source Voltage (V)

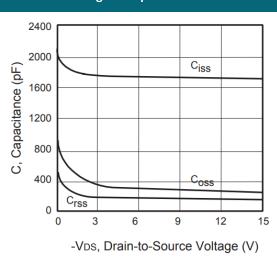


Fig. 4 • On-Resistance Variation with Temperature

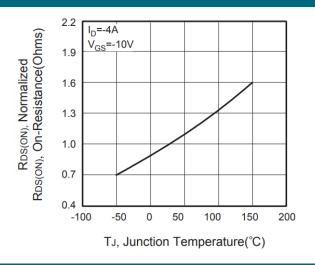


Fig. 5 • Gate Threshold Variation with Temperature

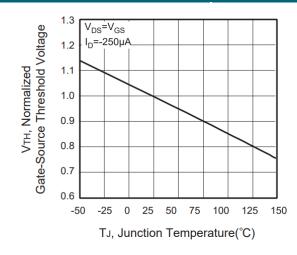
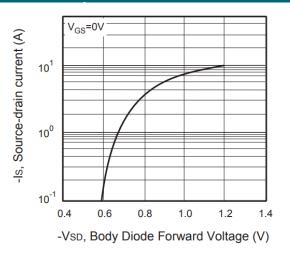


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



MGT ▲ Manufacturer Group of Technology



## REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

## Fig. 7 • Gate Charge

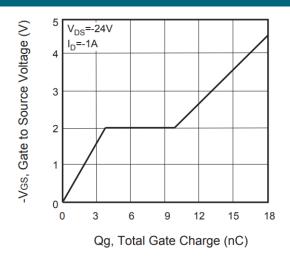


Fig. 8 • Maximum Safe Operating Area

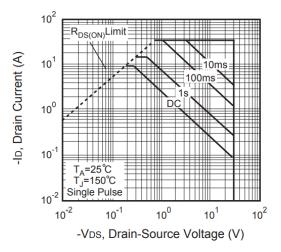


Fig. 9 • Breakdown Voltage Variation vs. Temperature

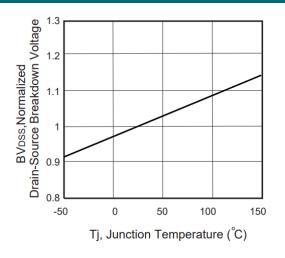


Fig. 10 • Switching Test Circuit

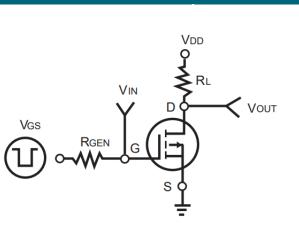
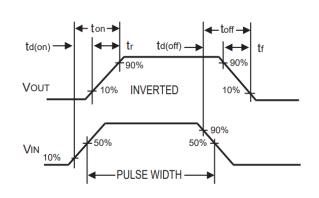


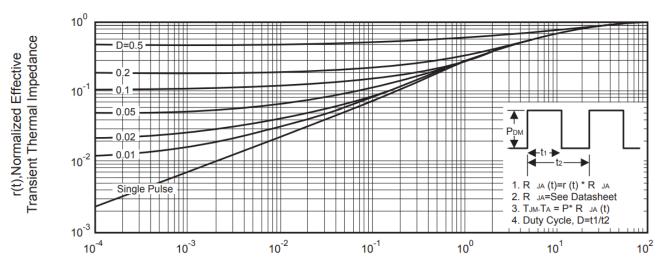
Fig. 11 • Switching Waveforms





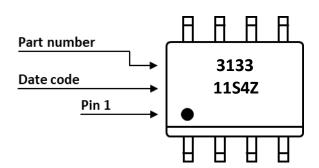
## REFERENCE DATA A TYPICAL DEVICE PERFORMANCE





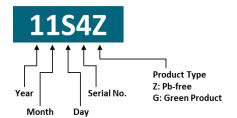
Square Wave Pulse Duration (sec)

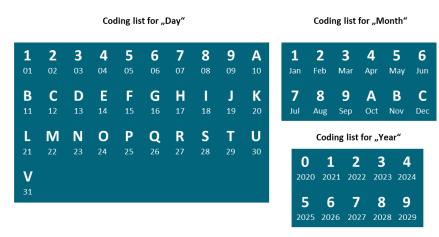
#### **PART MARKING**



#### **DATE CODE**

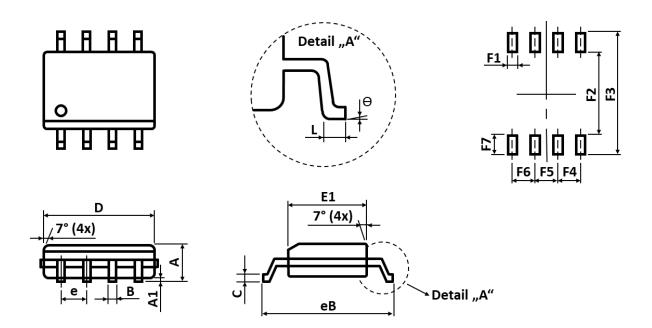
Example: 11S4Z







## PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	1.350	-	1.750
A1	0.100	-	0.250
В	0.310	-	0.510
С	0.170	-	0.250
D	4.690	-	5.000

Sym	Millimeters Millimeters (Min.) (Typ.)		Millimeters (Max.)
E1	3.700		4.060
еВ	5.800		6.200
е		1.270	
L	0.400		0.950
Θ	0°	-	8°

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
F1	_	0.500	_	
F2			-	
F3	-	6.250	-	
F4	-	1.270	-	

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	1.270	-
F6	-	1.270	-
F7	-	1.000	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

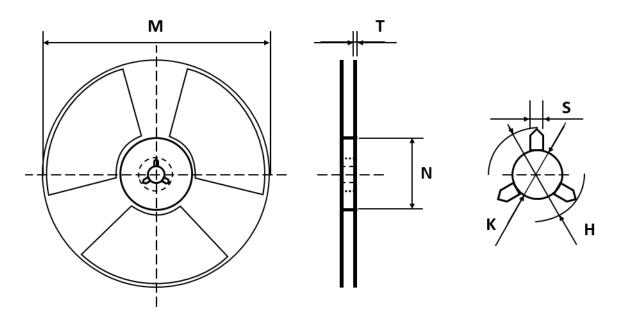
2. For further information, please reference document IPC-7351A.

## **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEM3133	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs

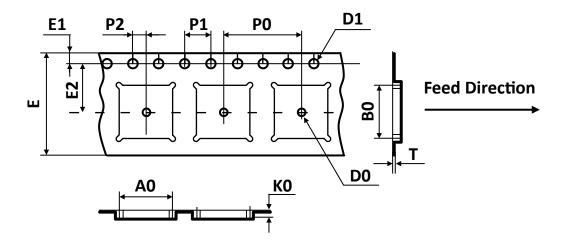


## **REEL DIMENSIONS** ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	K	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
12111111	<i>y</i> 550	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

## **TAPE DIMENSIONS** ▲ All dimensions in mm

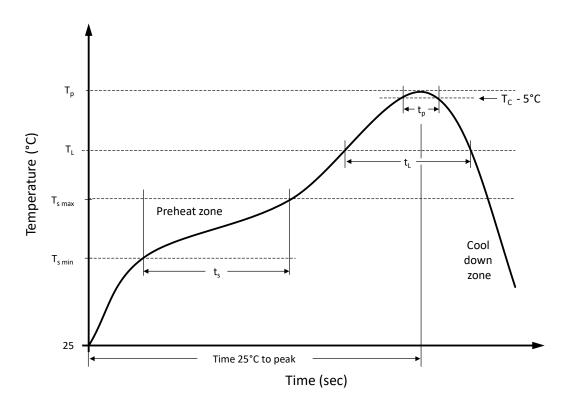


Packag	A0	В0	K0	D0	D1	E	E1	E2	Р0	P1	P2	T
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
308	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



## RECOMMENDED REFLOW SOLDERING PROFILE



## **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T <sub>s max</sub>	150 °C	200 °C
Preheat time t <sub>s</sub> from T <sub>s min</sub> to T <sub>s max</sub>	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	$T_L$	183 °C	217 °C
Time t <sub>L</sub> maintained above T <sub>L</sub>	t <sub>L</sub>	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate (T <sub>L</sub> to T <sub>p</sub> )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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